



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	John T. Moore et al.	§	Group Art Unit:	2811
Serial No.:	09/496,794	§		
Filed:	February 2, 2000	§	Examiner:	Douglas Owens
For:	Trench Isolation for Semiconductor Devices	§	Atty. Dkt. No.:	MCT-0005-D1-US 97-0608

Commissioner for Patents  
Washington DC 20231

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REPLY TO PAPER NO. 16

Sir:

In response to the office action mailed November 13, 2002, reconsideration is requested in view of the following remarks.

REMARKS

Claim 26 is rejected under § 102(b) based on Jang. Plainly the Section 102(b) rejection is improper since the Jang patent issued March 24, 1998 and the present application is based on the parent that was filed in 1997.

Moreover, the office action contends that Jang and the present application use the same materials for the trench filler material and the first material deposited on the support. The Examiner contends that the first material is 20 in the Jang reference. The Examiner contends that because the materials in the present application and the cited reference are the same that inherently the etch rate must be the same.

However, Jang does not disclose the same materials. For example, for the pad oxide 20, Jang indicates that it can be formed by "wet thermal oxidation." See Jang, column 4, line 67. In

Date of Deposit: January 9, 2003

I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as **first class mail** with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, Washington DC 20231.

*Cynthia L. Hayden*  
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